Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Low threshold voltage
- Extended temperature range T_i = 175 °C
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 500 V HBM (class H1B)
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	7	Α
Static charac	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 7 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	15	19	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain	TO-236AB (SOT23)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV15UNEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMV15UNEA	%GN

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	7	А
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	4.4	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	28	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	610	mW
			[1]	-	1.4	W
		T _{sp} = 25 °C		-	8.3	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-drain d	iode		•	<u>'</u>		
Is	source current	T _{amb} = 25 °C	[1]	-	1.4	Α
ESD maximum	rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	500	V
Avalanche rug	gedness			'		,
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	T _{j(init)} = 25 °C; I _D = 1.5 A; DUT in avalanche (unclamped)		-	14	mJ

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 2 .
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

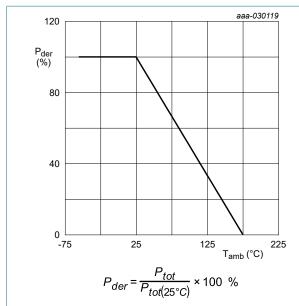


Fig. 1. Normalized total power dissipation as a function of ambient temperature

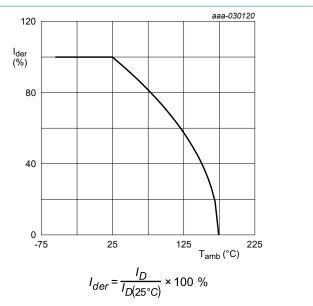


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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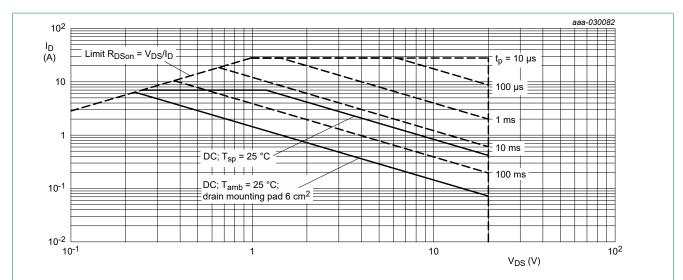


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	208	245	K/W
	junction to ambient		[2]	-	88	104	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	13	18	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

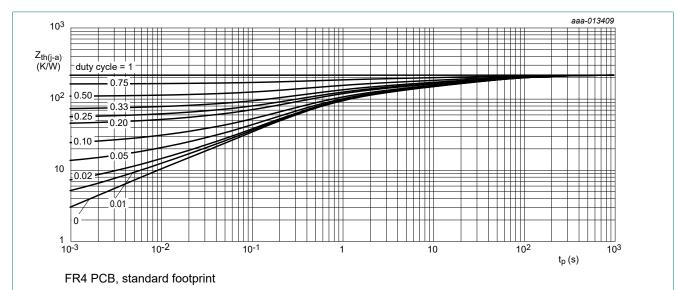


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

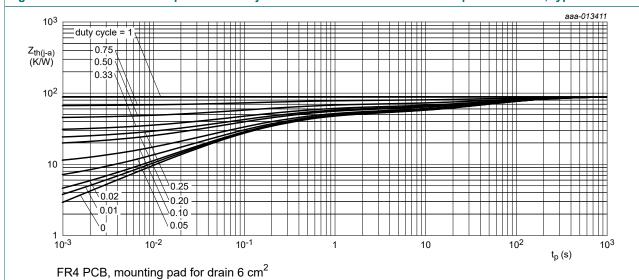


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.65	0.9	V
I _{DSS}	drain leakage current	V _{DS} = 20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 7 A; T _j = 25 °C	-	15	19	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 7 A; T _j = 175 °C	-	28	35	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 5.7 \text{ A}; T_j = 25 \text{ °C}$	-	18	24	mΩ
		V _{GS} = 1.8 V; I _D = 2 A; T _j = 25 °C	-	23	36	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 7 \text{ A}; T_j = 25 \text{ °C}$	-	50	-	S
R_G	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic ch	aracteristics		'			1
Q _{G(tot)}	total gate charge	V _{DS} = 10 V; I _D = 6 A; V _{GS} = 4.5 V;	-	11	17	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.3	-	nC
Q_{GD}	gate-drain charge		-	2.1	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	1220	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	124	-	pF
C _{rss}	reverse transfer capacitance		-	102	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 10 V; I _D = 6 A; V _{GS} = 4.5 V;	-	10	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	24	-	ns
t _{d(off)}	turn-off delay time		-	32	-	ns
t _f	fall time]	-	34	-	ns
Source-drai	in diode					•
V_{SD}	source-drain voltage	$I_S = 1.4 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.7	1.2	V
t _{rr}	reverse recovery time	$I_S = 1.5 \text{ A}; dI_S/dt = -100 \text{ A/µs};$	-	10	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 10 \text{ V}; T_j = 25 \text{ °C}$	-	2	-	nC

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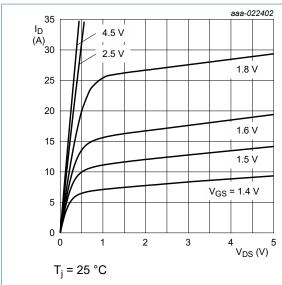


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

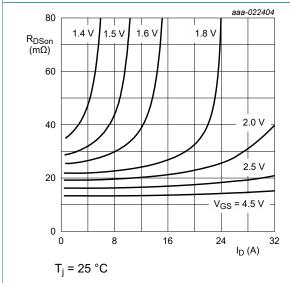


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

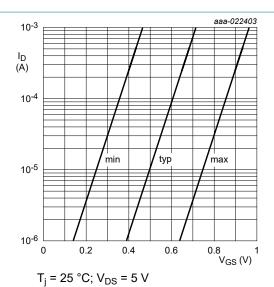


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

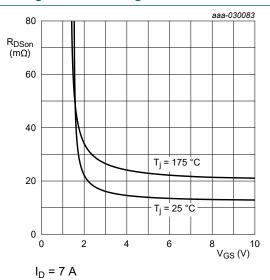


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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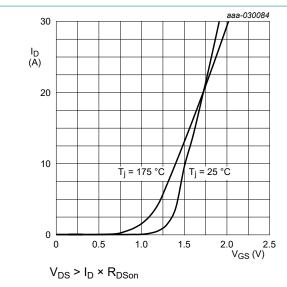


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

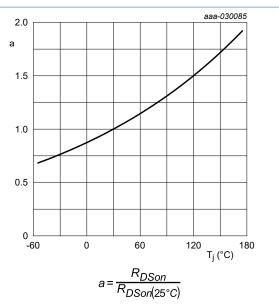


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

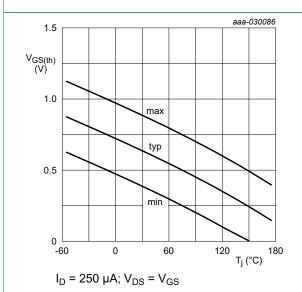
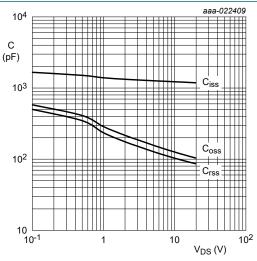


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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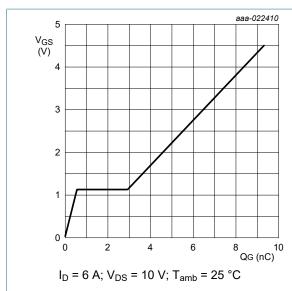


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

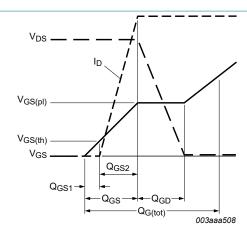


Fig. 15. Gate charge waveform definitions

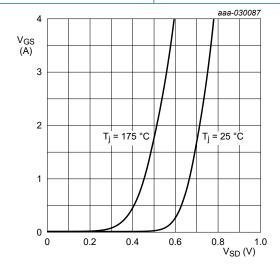
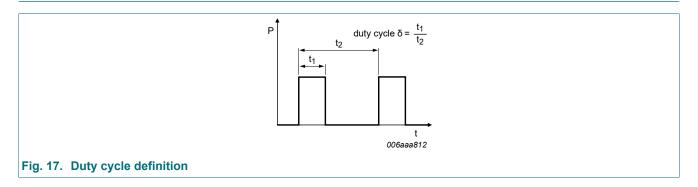


Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

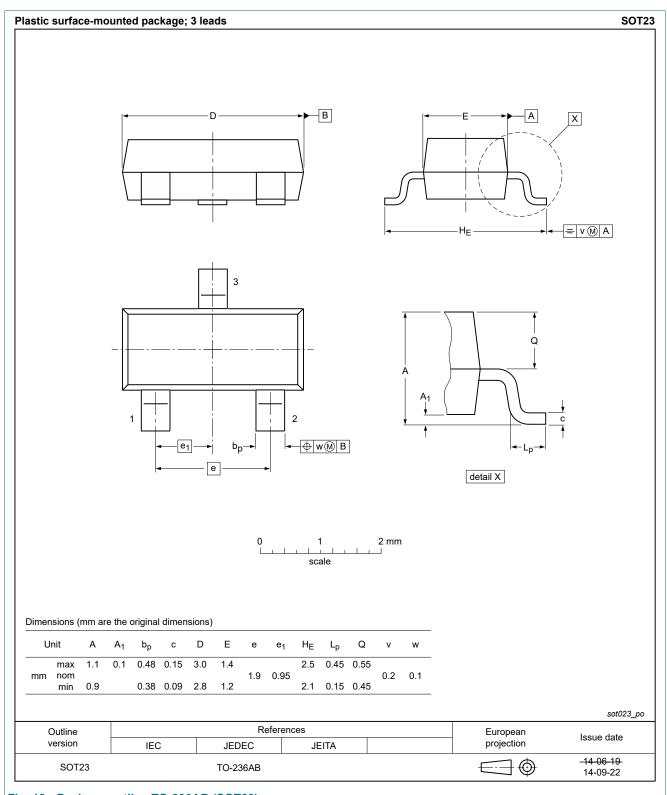
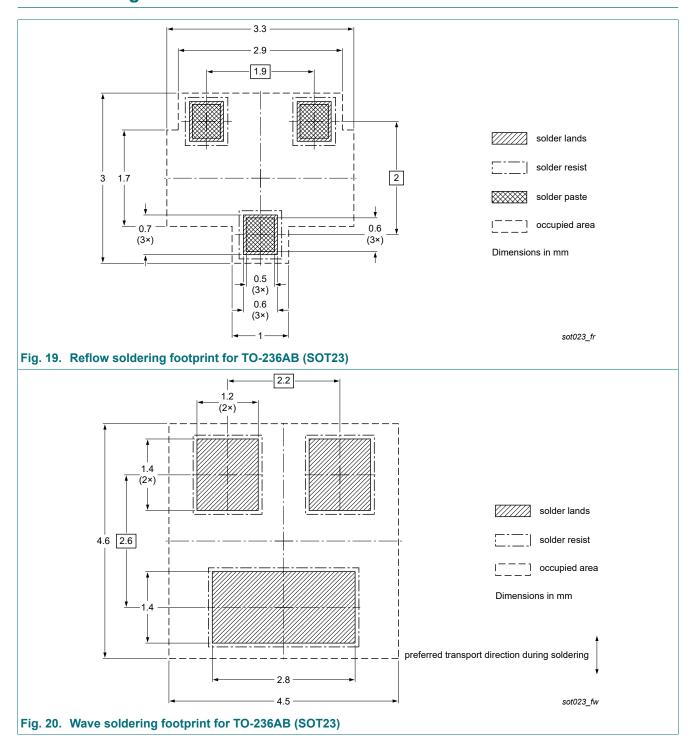


Fig. 18. Package outline TO-236AB (SOT23)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV15UNEA v.1	20190906	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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